High Hole-Mobility Molecular Layer Made from Strong Electron Acceptor Molecules with Metal Adatoms

Hiroyuki Yamane,*†§ and Nobuhiro Kosugi‡†

†Institute for Molecular Science, National Institutes of Natural Sciences, Myodaiji, Okazaki 444-8585, Japan
‡SOKENDAI (The Graduate University for Advanced Studies), Myodaiji, Okazaki 444-8585, Japan

Supporting Information

ABSTRACT: The electronic structure of 7,7,8,8-tetracyanoquinodimethane (TCNQ) and 2,3,5,6-tetrafluoro-TCNQ (F4TCNQ) monolayers on Au(111) has been investigated by means of angle-resolved photoemission spectroscopy (ARPES) with synchrotron radiation. In contrast to the physisorbed TCNQ/Au(111) interface, the high-resolution core-level photoemission spectra and the low-energy electron diffraction at the F4TCNQ/Au(111) interface show evidence for the strong charge transfer (CT) from Au to F4TCNQ and for the Au atom segregation from the underlying Au(111) surface, suggesting a possible origin of the spontaneous formation of the two-dimensional F4TCNQ-Au network. The ARPES experiment reveals a low hole-injection barrier and large band dispersion in the CT-induced topmost valence level of the F4TCNQ-Au network with 260 meV bandwidth due to the adatom-mediated intermolecular interaction. These results indicate that strong electron acceptor molecules with metal adatoms can form high hole-mobility molecular layers by controlling the molecule–metal ordered structure and their CT interaction.

Two-dimensional (2D) atomic/molecular networks, e.g., graphene and supramolecular macrocyclic systems, and their layer-by-layer assemblies have attracted much attention for potential applications in (opto)electronics and energy storage because of their low-dimensional electronic systems and nanoporous structures.1–4 In order to fabricate functional molecular layers based on the selective assembly of the 2D network, the ordered structure of molecules, which dominates anisotropic physical and chemical properties, has to be designed by considering the molecular symmetry and the intermolecular interaction such as van der Waals, electrostatic, exchange, polarization, and charge-transfer (CT) interactions. Indeed, a large variety of molecular systems such as metal–organic frameworks (MOF) and covalent organic frameworks (COF) have been designed, and their 2D thin-film fabrications have been developed as a challenging issue.

Here, we shed light on the CT interaction in archetypical organic semiconductors. 7,7,8,8-Tetracyanoquinodimethane (TCNQ) and 2,3,5,6-tetrafluoro-TCNQ (F4TCNQ) are well-known as electron acceptor molecules with large electron affinity and have been anticipated for the CT complex in combination with electron donor molecules,5,6 for the p-type doping of molecules,7,8,9 and for the control of the interfacial charge-injection barrier with respect to the highest occupied molecular orbital (HOMO) and/or the lowest unoccupied molecular orbital (LUMO).10–18 The cyano group in TCNQ derivatives plays a crucial role in the strong electron-accepting ability in the CT interaction and often induces the intra- and/or inter-molecular structural relaxations such as the molecular distortion16–18 and the 2D network formation,19–22 depending on metal atoms and underlying surfaces; especially, the F4TCNQ molecules on an Au(111) surface show both evidence for the strong molecular distortion and for the spontaneous formation of the 2D network via the cyano group with the Au adatom segregated from the underlying Au(111) surface as demonstrated using scanning tunneling microscopy (STM).23,24

Molecule–metal coordination systems have a large degree of freedom for the design of the 2D network structure and its functionalities. In order to understand characteristics of the 2D TCNQ-metal network systematically, we have studied the geometric and electronic structures of the F4TCNQ/Au(111) and TCNQ/Au(111) interfaces as a benchmark by using low-energy electron diffraction (LEED) and angle-resolved photoemission spectroscopy (ARPES) with synchrotron radiation. We have succeeded in the observation of large in-plane band dispersion for the F4TCNQ-derived electronic states, which are formed just below the Fermi level (E F) by the strong CT from the Au atom to the F4TCNQ molecule. The observed electronic interaction in the F4TCNQ-Au network satisfies the high hole concentration (n) due to the low hole-injection barrier and also the high hole mobility (μ) due to the large band dispersion in the conductivity formula σ = neμ.

Received: September 8, 2017
Accepted: October 18, 2017
Published: October 18, 2017

DOI: 10.1021/acs.jpclett.7b02390
As mentioned above, the cyano group in TCNQ derivatives plays a crucial role in the CT interaction. The strong CT interaction at the F4TCNQ/Au(111) interface is clearly detected by the high-resolution N 1s photoemission spectra. As shown in Figure 1a, a neutral N 1s peak (labeled N0) appears at the binding energy (E_b) of 398.5 eV for the 1 ML (monolayer) TCNQ on Au(111), indicating the physisorptive interaction at the TCNQ/Au(111) interface. On the other hand, the 1 ML F4TCNQ on Au(111) shows a predominant N 1s peak at E_b = 397.6 eV, which is lower than the N0 peak in energy and is ascribed to the negatively charged N 1s (labeled N−) due to the CT interaction at the interface. The N− peak is observable also for the 2 ML F4TCNQ on Au(111) together with the N0 peak, corresponding well with the concept of the extended space charge region for the F4TCNQ multilayer on Au(111).25,26 The strong CT interaction in general contributes to the ordered structure of the molecules. The LEED images in Figure 1b exhibit that the F4TCNQ and TCNQ molecules on Au(111) form the different ordered structures to each other with the commensurate \( \left( \frac{5}{1} \frac{2}{3} \right) \) structure for the F4TCNQ/Au(111) interface and the incommensurate \( \left( \frac{3}{2} \frac{3}{4} -0.5 \right) \) structure for the TCNQ/Au(111) interface as shown in Figure 1c, as previously reported.\(^{23-26}\) We found that the LEED image of the F4TCNQ/Au(111) interface does not show the well-known 22 \( \times \sqrt{3} \) herringbone pattern of the Au(111) surface just around the (0,0) spot, which is clearly observable at the physisorbed TCNQ/Au(111) interface. Furthermore, we observed that the Au 4f7/2 photoemission line shape for the F4TCNQ/Au(111) interface is slightly broader than that for the TCNQ/Au(111) interface because of the appearance of the new peak component at the low E_b side (Figure S1 in the Supporting Information). The observed Au 4f7/2 photoemission line shape can be reproduced by considering the surface core-level shift due to the presence of bulk, surface, and adatom Au sites. These results support the validity of the present sample preparation in accordance with the earlier STM observation of the formation of the F4TCNQ-Au network based on the Au atom segregation from the Au(111) surface by the strong CT interaction between F4TCNQ and Au.\(^{24}\) As illustrated in Figure 1c, 1-F4TCNQ molecule and 1-Au adatom exist in the oblique unit cell of the F4TCNQ-Au network, where F4TCNQ molecules are 2-fold coordinated with Au adatoms.

In addition to the ordered structure, the CT interaction introduces the significant change in the work function (\( \Phi \)) and the valence electronic structure. Figure 2a shows the normal-emission ARPES spectra [emission angle (\( \theta \)) of 0 \( \sim \pm 7^\circ \) integrated] measured for the F4TCNQ/Au(111) interface. The secondary-electron cutoff for the F4TCNQ/Au(111) interface, shown in the left panel of Figure 2a, shifts to the higher E_b side from that for the clean Au(111) surface. This higher-E_b shift indicates the decrease in \( \Phi \) upon the adsorption of TCNQ due to the Pauli repulsion (i.e., exchange interaction) of surface electrons at the interface (\( \Delta \Phi = -0.34 \) eV). The opposite trend is observed for the F4TCNQ/Au(111) interface, giving the shift in the secondary-electron cutoff to the lower E_b side upon adsorption of F4TCNQ, i.e., the increase in \( \Phi \), due to CT from Au to F4TCNQ (\( \Delta \Phi = +0.27 \) eV), which overwhelms the contribution of the Pauli repulsion.

At the valence-band region for the F4TCNQ/Au(111) interface (right panel of Figure 2a), the broad F 2p peak appears at E_b = 10.4 eV, and the CT-induced valence peaks appear just below E_b; E_b = 0.5 eV (labeled CT1) and 1.5 eV (labeled CT2), which can be ascribed to the filled LUMO due to CT and the former HOMO, respectively.\(^{21,22}\) Furthermore, the Shockley-type surface state of Au(111) (labeled S) is almost quenched at the F4TCNQ/Au(111) interface because of the significant electronic modification by F4TCNQ as discussed later. On the other hand, the TCNQ-derived peak is not observable just below E_p and the Shockley state is weakly modified with the shift to the lower E_b side at the TCNQ/Au(111) interface. It has been understood that the modification...
of the Shockley state by adsorbates is derived from the rearrangement of surface electron systems by complex interfacial interactions. The lateral energy versus wavevector \((E-k)\) map of the Shockley state is shown in Figure 2b as obtained using the relation of

\[
k_{\parallel} = \left[2m_0(h\nu - E_b - \Phi)\right]^{1/2}\sin \theta/\hbar
\]

where \(m_0\) is the free-electron mass. The Shockley state at the TCNQ/Au(111) interface shows a weak modification with the upshift by \(\Delta E_b = 170\) meV from that at the clean Au(111) surface, which is in general ascribed to the Pauli repulsion of surface electron systems. At the F4TCNQ/Au(111) interface, the bottom tail of the Shockley state is barely observable at \(E_b = 0\) eV and \(k_\parallel = 0\) Å\(^{-1}\); in other words, the large upshift by more than 465 meV is induced as a result of the significant electronic modification due to the strong CT interaction at the interface. As demonstrated previously, the observed shift in the Shockley state enables us to determine the interfacial adsorption energies, only \(18.0\) meV/Å\(^2\) (= 0.106\(\Delta E_b\)) for the TCNQ/Au(111) interface, suggesting again the weak physisorptive interaction, and more than \(49.3\) meV/Å\(^2\) for the F4TCNQ/Au(111) interface, which involves various interfacial electronic interactions.

In order to discuss the interfacial electronic interaction in more detail, the \(\theta\)-dependent ARPES spectra along the high-symmetry \(\Gamma-K-M\) and \(\Gamma-M\) directions are shown in Figure 3. The clean Au(111) surface at 20 K shows the well-known electronic band dispersion for the Shockley state \((S)\) around \(\theta = 0^\circ\), sp band around \(\theta = 20^\circ\), and 5d band in full-\(\theta\) region. At the TCNQ/Au(111) interface at 20 K, the HOMO-derived peak is observable behind the Au 5d band at the constant \(E_b\) position with \(\theta\) (\(E_b = 2.6\) eV), and a quite weak signal from the deeper lying TCNQ-derived electronic state (HOMO-1) can be seen at \(E_b = 4.0\) eV at \(\theta = 20^\circ-30^\circ\). The energy separation between HOMO and HOMO-1 by \(1.4\) eV corresponds well with the electronic structure of the TCNQ thick film. The nondispersive HOMO and HOMO-1 peaks indicate the localized molecular electronic states at the TCNQ/Au(111) interface, while the CT-induced peaks (CT\(_1\) and CT\(_2\)) at the F4TCNQ/Au(111) interface at 20 K show a large dispersion with \(\theta\), which is direct evidence for the delocalization of molecular electronic states. As shown in Figure 3c, the CT-induced peaks are getting visibly clearer at the higher \(\theta\) (\(k_{\parallel}\)) region, which is the reflection of the orbital-specific spatial electron distribution in ARPES. The CT\(_1\) peak appears at \(E_b = 0.41\) eV when \(\theta = 27^\circ\). With increasing \(\theta\), the CT\(_1\) peak shifts to the higher \(E_b\) side and turns back at around \(\theta = 32^\circ\). The inflection point is also found at various \(\theta\) such as \(38^\circ\). Moreover, the dispersive behavior for the CT-induced peaks is observable not only at 20 K but also at 300 K (Figure S2).

The LEED analysis for the F4TCNQ/Au interface using LEEDpat 4.2,\(^{31}\) shown in Figure 4a, yields two domains of the F4TCNQ-Au network structure that are rotated with respect to

![Figure 4. Valence-band dispersion at the F4TCNQ/Au(111) interface.](image)
the reciprocal unit cell of the 6-fold symmetric Au(111) surface. The multidomain overlayer structure introduces the intricate surface Brillouin zone (SBZ) as displayed in Figure 4b; therefore, it is in principle difficult to characterize the observed band dispersion for the multidomain films precisely. Remarkably, the $E-k_F$ map of the F$_4$TCNQ/Au(111) interface at 20 K along the high-symmetry $\Gamma$-M direction ($k_M$), shown in Figure 4c, reveals the simple dispersion curves with a single component for the CT-induced states, probably due to the matrix element effect in ARPES. Indeed, the CT$_1$ and CT$_2$ band dispersion curves get complex if the $E-k_F$ measurement is not performed along the high-symmetry directions (Figure S3).

The intensity of CT$_1$ is weaker than that of CT$_2$ at the low $k_M$ region (top panel of Figure 4c), and their relative intensity gets flipped at the higher $k_M$ region (bottom panel of Figure 4c), indicating different spatial electron distributions between the filled LUMO (CT$_1$) and the former HOMO (CT$_2$). From the line profile analysis for the CT$_1$-band dispersion at $k_M = 0.06$ Å$^{-1}$, the dispersion center, bandwidth, and dispersion periodicity are determined as 0.57 ± 0.01 eV, 260 ± 10 meV, and 0.54 ± 0.02 Å$^{-1}$, respectively. The threshold $E_k$ position for the CT$_1$ band is determined to be 0.18 eV. The same dispersion periodicity is determined from the CT$_2$ band dispersion with the narrower bandwidth of 180 ± 10 meV. These dispersion curves give the first zone boundary at $k_M = 0.27 ± 0.02$ Å$^{-1}$, in good agreement with the SBZ boundary determined from LEED as shown in Figure 4b; therefore, the observed dispersion can be ascribed to the F$_4$TCNQ-Au network structure and its electronic interaction.

The observed bandwidth for CT$_1$ by 260 ± 10 meV is comparable to the previously observed lateral band dispersions using ARPES for flat-lying organic monolayers on noble metal surfaces, which are categorized as the substrate-mediated band dispersion, e.g., 250 meV for pentacene on Cu(110), 90 meV for iron and cobalt phthalocyanine (FePc and CoPc) on Au(110), 230 meV for perylene-3,4,9,10-tetracarboxylic dianhydride (PTCDA) on Ag(110), >500 meV for PTCDA on Cu(100), 150 meV for naphthalene-1,4,5,8-tetracarboxylic dianhydride (NTCDA) on Ag(110), and 200 meV for NTCDA on Cu(110). The strong CT interaction between F$_4$TCNQ and Au could play a main role in the present large band dispersion and also introduce the decrease in the hole-injection barrier at the upper branch of the filled-LUMO band (CT$_1$). The free-electron-like parabolic fitting to the observed dispersion around the $\Gamma$ point enables us to determine the hole effective mass ($m^*$) as 0.46$m_0$ for CT$_1$, and 0.71$m_0$ for CT$_2$, both of which are heavier than that for Au sp band (0.27$m_0$) (Figure S4). According to the Bader analysis in the electron density distribution, 0.9 electrons contribute to the CT interaction in the F$_4$TCNQ-Au/Au(111) system and 0.29 and 0.61 electrons transfer from the Au(111) surface and the segregated Au adatom, respectively. The heavier $m^*$ for CT$_1$ with respect to the Au sp band thus suggests that the observed dispersion mainly originates not from the “pure” substrate-mediated intermolecular interaction but from the adatom-mediated intermolecular interaction, which is invisible at the TCNQ/Au(111) interface. It was reported that a TCNQ-Mn network film on Ag(001), prepared by the vacuum deposition for both TCNQ and Mn, does not show the band dispersion for molecular electronic states, although the CT-derived peaks are formed just below $E_F$. It was inferred that the lateral distance is too large in the ordered structure to mediate a significant lateral intermolecular interaction in the TCNQ-Mn network. The metal—atom segregation from the underlying substrate might be one of promising methods to fabricate functional molecule—metal coordination networks, where the electron affinity and the functional group in the molecule play a crucial role, as demonstrated in the present work. Considering the large degree of freedom for the design of the 2D network structure, the present observation for the delocalized CT band in the F$_4$TCNQ-Au/Au(111) system suggests possible realization of highly efficient molecular spintronic devices by choosing organic radicals or magnetic atoms in 2D molecule—metal hybrid networks, under adequate control of the network structure to delocalize molecular electronic states.

Finally, we briefly discuss the largely dispersive band at $k_M = 0.06$ Å$^{-1}$ (labeled X in Figure 4c), which is also observable in the raw ARPES spectra in Figure 3d as a quite weak signal at $\theta = 0°-10°$. If band X originates from a genuine molecular electronic state of the F$_4$TCNQ-Au network, it should appear with the same $k_F$ periodicity for the CT$_1$ and CT$_2$ bands. Because band X appears only around the $\Gamma$ point, band X can be ascribed to the replica of the Au sp band due to the surface Umklapp scattering by the overlayer’s lattice. Further investigation using the low-$hv$ beam in ARPES is necessary for more confident assignment of band X.

In conclusion, the geometric and electronic structures of the F$_4$TCNQ-Au network, which is spontaneously formed at the F$_4$TCNQ/Au(111) interface, have been studied by means of LEED and ARPES with synchrotron radiation in comparison with the physisorbed TCNQ/Au(111) interface. The high-resolution core-level photoemission spectra and the LEED image of the F$_4$TCNQ/Au(111) interface comprehensively support the earlier finding of the F$_4$TCNQ-Au network formation, originating from the Au atom segregation due to the CT interaction. Through the strong electron-accepting molecular functionality of F$_4$TCNQ, the CT interaction from Au to F$_4$TCNQ introduces the filling of LUMO, and the CT-induced electronic states are of temperature-independent delocalized character due to the stable adatom-mediated intermolecular interaction, as revealed from the ARPES experiments. The resultant filled-LUMO band has the characteristics of (i) the low hole-injection barrier by the threshold $E_k$ of 0.18 eV and (ii) the large bandwidth by 260 ± 10 meV with $m^*_0 = 0.46$m$_0$ at the $\Gamma$ point, both of which satisfy the conductivity formula $\sigma = ne\mu m$ as the high hole-mobility 2D molecular layer. All of the above characteristics are not observable at the TCNQ/Au(111) interface. The present finding can be a benchmark for the development of novel functional molecular materials based on molecule—metal coordination networks.

# EXPERIMENTAL METHODS

The present ARPES experiment was performed on a highly brilliant in-vacuum undulator beamline BL6U of the UVSOR-III Synchrotron in the Institute for Molecular Science (Okazaki, Japan). The BL6U covers the photon energy from 40 to 800 eV with a photon flux of ca. 10$^{11}$ photons/sec under the top-up operation. The ARPES endstation at BL6U consists of the measurement, preparation, and load-lock chambers in UHV.

The clean Au(111) substrate was obtained by repeated cycles of Ar$^+$ sputtering and the subsequent annealing at 700 K, as confirmed by LEED with a microchannel-plate (MCP) detector and by the Shockley state in ARPES. In order to obtain the ordered monolayers of F$_4$TCNQ and TCNQ on Au(111), the
thin multilayer sample with the layer thickness of ca. 50 Å was heated at above the multilayer desorption temperature of 380 K, which is slightly lower than the desorption temperature of the F₄TCNQ and TCNQ monolayers on Au(111), as confirmed by ARPES (Figure S5). The lateral ordered structure of organic layers was confirmed by MCP-LEED.

The ARPES spectra were acquired from the energy versus angle image by using the MCP detector of a hemispherical electron energy analyzer (MB Scientific A-1). All ARPES spectra shown in this Letter were measured at 20 K by using the liquid He cryostat (Janis ST-400-UHV) in the six-axes (x, y, z polar, and azimuth) manipulator. For the secondary-electron-cutoff (i.e., work function) measurement in ARPES, the negative bias of −5,000 V was applied to the sample to observe photoelectrons close to the zero-kinetic energy. The E₀ position for the valence-band and core-level ARPES spectra was calibrated by measuring the E₀ edge and the Au 4f peak of the underlying Au(111) substrate, respectively.

■ ASSOCIATED CONTENT

Supporting Information
The Supporting Information is available free of charge on the ACS Publications website at DOI: 10.1021/acs.jpclett.7b02390.

Extra experimental data and corresponding discussion; high-resolution Au 4f/2 photoemission spectra, temperature dependence of ARPES, azimuthal-angle dependence of the CT-band dispersion, fitting analysis of the CT-band dispersion, and annealing-temperature dependence of ARPES (PDF)

■ AUTHOR INFORMATION

Corresponding Author
*E-mail: yamane@spring8.or.jp.

ORCID
Hiroyuki Yamane: 0000-0002-8023-7918

Present Address

Notes
The authors declare no competing financial interest.

■ ACKNOWLEDGMENTS

The authors thank the staff of the UVSOR-III Synchrotron for their kind support in the present ARPES experiment. This work is supported by Grant-in-Aid for Scientific Research on Innovative Areas (π-System Figuration: Control of Electron and Structural Dynamism for Innovative Functions) JP17H05167 and Grant-in-Aid for Scientific Research (C) JP17K05767 from Japan Society for the Promotion of Science (JSPS) and Grant for Basic Science Research Projects from the Sumitomo Foundation 150301.

■ REFERENCES


(31) Hermann, K. E.; Van Hove, M. A. LEEDpat, version 4.2; 2014; see also http://www.fhi-berlin.mpg.de/KHsoftware/LEEDpat/index.html.


